

What is claimed is:

1. A method for forming a pattern of a semiconductor device, comprising the steps of:
 - (a) sequentially forming a base layer to be patterned, a lower photoresist layer, a blocking layer and an upper photoresist layer on a substrate;
 - (b) forming the first photoresist pattern on the upper photoresist layer, and etching the blocking layer according to the first photoresist pattern;
 - (c) forming the second photoresist pattern on the lower photoresist layer, which is opened by the spacing of the first photoresist pattern, wherein the spacing of the first photoresist pattern is greater than a line width of the second photoresist pattern;
 - (d) etching the base layer using the second photoresist pattern as a mask; and
 - (e) stripping the remaining photoresist layer.
2. The method for forming a pattern of a semiconductor device of claim 1, wherein the etched blocking layer prevents the lower photoresist layer under the blocking layer from being removed in the second photoresist pattern forming step.
3. The method for forming a pattern of a semiconductor device of claim 1, wherein the blocking layer is made of an insulating layer.
4. The method for forming a pattern of a semiconductor device of claim 1, wherein the blocking layer is an anti-reflection layer.
5. The method for forming a pattern of a semiconductor device of claim 1, wherein the lower photoresist layer and the upper photoresist layer are produced with a positive photoresist.

6. The method for forming a pattern of a semiconductor device of claim 1, wherein a spacing produced by the second photoresist pattern is less than the resolution limit of a lithographic process.

7. The method for forming a pattern of a semiconductor device of claim 1, wherein a spacing produced by the first photoresist pattern **S1** is equal to **2S2+W2**, wherein **S2** represents a spacing produced at each side of the second photoresist pattern, and **W2** represents a line width of the second photoresist pattern.